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Complete if known Spostitute for form 1449/PTO **Application Number** 10/672,961 (Conf. No.: 9439) INFORMATION DISCLOSURE Filing Date September 26, 2003 First Named Inventor Glenn J. Leedy STATEMENT BY APPLICANT Art Unit 2822 **Examiner Name Monica Lewis** (use as many sheets as necessary) Sheet of Attorney Docket Number ELM-2 Cont. 4

U.S. PATENT DOCUMENTS									
Examiner	Cite	Document Number	Publication Date	Name of Patentee or	Pages, Columns, Lines, Where Relevant Passages or Relevant				
initials*	No.'	Number - Kind Code ² (If known)	MM-DD-YYYY	Applicant of Cited Documents	Figures Appear				
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All References Have Been Considered:

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SUPPLEMENTAL INFORMATION **DISCLOSURE** STATEMENT BY APPLICANT

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10/672,961 Application Number September 26, 2003 Filing Date First Named Inventor Glenn.J. Leedy 2822 Art Unit Monica Lewis Examiner Name Attorney Docket Number ELM-2 Cont. 4

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Subs	stitute for form 1449A/B/PT	ro			Complete if Known
			•	Application Number	10/672,961
SUF	PPLEMENTA	L INFO	DRMATION	Filing Date	September 26, 2003
	DISCL	OSUR	E	First Named Inventor	Glenn J. Leedy
S	TATEMENT	BY AP	PLICANT	Art Unit	2822
				Examiner Name	Monica Lewis
Sheet	2	of	3	Attorney Docket Number	ELM-2 Cont. 4

		NON PATENT LITERATURE DOCUMENTS	
Examiner Initials	Cite No.1	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T²
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